

ABSTRACT OF THE DISCLOSURE

A capacitor construction includes a first electrode and a layer between the first electrode and a surface supporting the capacitor construction. The capacitor construction can exhibit a lower RC time constant compared to an otherwise identical capacitor construction lacking the layer. Alternatively, or additionally, the first electrode may contain Si and the layer may limit the Si from contributing to formation of metal silicide material between the first electrode and the supporting surface. The layer may be a nitride layer and may be conductive or insulative. When conductive, the layer may exhibit a first conductivity greater than a second conductivity of the first electrode. The capacitor construction may be used in memory devices.